

Model Comparison

Model	VRRM VDRM(V)	ITAVIFAV(A)
C3PDB175N08	800	175
C3PDB175N12	1200	175
C3PDB175N14	1400	175
C3PDB175N16	1600	175
C3PDB175N18	1800	175

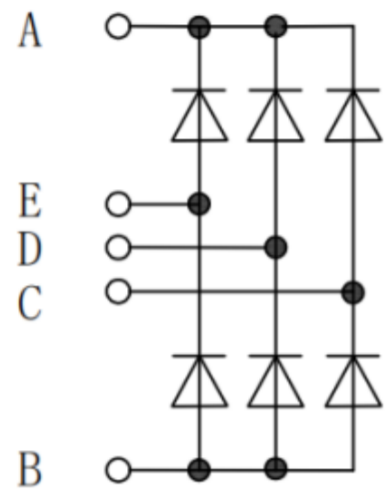
Features / Advantages

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

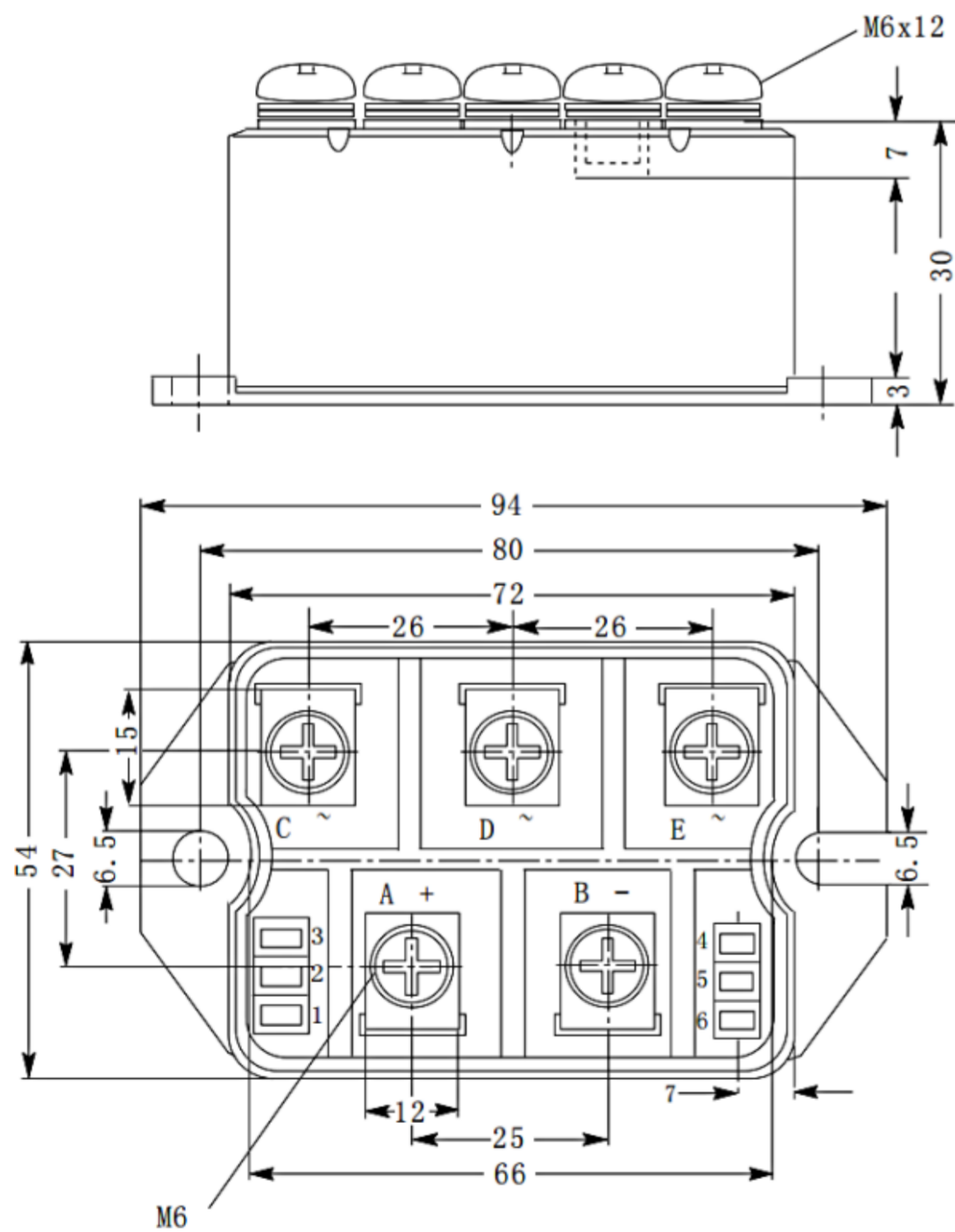
Applications

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Internal Circuit



Package Dimension Dimensions in Millimeters



Parameters

Parameters	C3PDB175N08~18
V_{DRM} V_{RRM}	800~1800V
I_{dAV} @TC	175A
T_C	110°C
I_{FSM} 10ms, 45°C	1800A
$V_{(FO)}$ @ T_{vj} max	0.77V
Package style Outline drawings	XFA